



Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
30V	31mΩ @ V _{GS} = 10V	5.4A
300	45mΩ @ V _{GS} = 4.5V	4.5A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Battery charging
- Power-management functions
- DC-DC converters
- Portable power adaptors



Top View

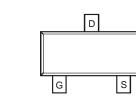
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View

Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nulliber	Fackage	Qty.	Carrier	
DMN3032L-7	SOT23	3,000	Tape & Reel	
DMN3032L-13	SOT23	10,000	Tape & Reel	

D

S

Internal Schematic

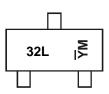
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{32L}{YM} = \text{Product Type Marking Code}$ $\frac{YM}{Y} = \text{Date Code Marking}$ $\frac{Y}{Y} = \text{Year (ex: K = 2023)}$ M = Month (ex: O = October)

M = Month (ex: O = Octor)

Date Code Key

Notes:

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	Ν	Р	R	S	Т	U	V	W
	-							_		-		
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			Vdss	30	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) $V_{GS} = 10V$ Steady State T _A = +25°C T _A = +70°C			lo	5.4 4.3	A
Pulsed Drain Current (Pulse width 10µs, Duty C	Pulsed Drain Current (Pulse width 10µs, Duty Cycle 1%)			30	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	0.8	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	Reja	150	°C/W
Power Dissipation (Note 5)	PD	1.3	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	Reja	93	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			- 71-			
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS		_	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(th)	1.0	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Deserver	_	22	31	mΩ	V _{GS} = 10V, I _D = 5.8A
Static Drain-Source On-Resistance	RDS(ON)	_	28	45	mc2	V _{GS} = 4.5V, I _D = 4.8A
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	481	_	pF	
Output Capacitance	Coss	_	51	_	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	Crss	_	42		pF	
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5	_	nC	
Total Gate Charge (V _{GS} = 10V)	Qg	_	10.1	—	nC	V _{DS} = 15V
Gate-Source Charge	Qgs	_	1.3	—	nC	I _D = 5.8A
Gate-Drain Charge	Q _{gd}		1.5	_	nC]
Turn-On Delay Time	td(ON)	_	3.2		ns	
Turn-On Rise Time	tR	_	18.3		ns	V _{DD} = 15V, V _{GS} = 10V
Turn-Off Delay Time	tD(OFF)		16.9	_	ns	$R_L = 2.6\Omega, R_g = 3\Omega$
Turn-Off Fall Time	tF	_	13.4		ns	7

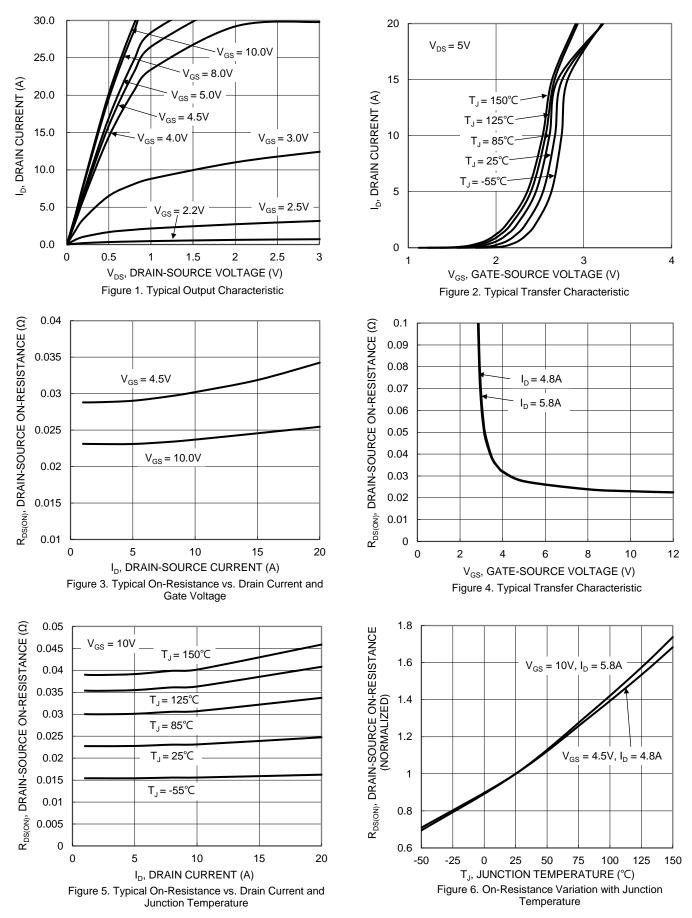
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Short duration pulse test used to minimize self-heating effect.

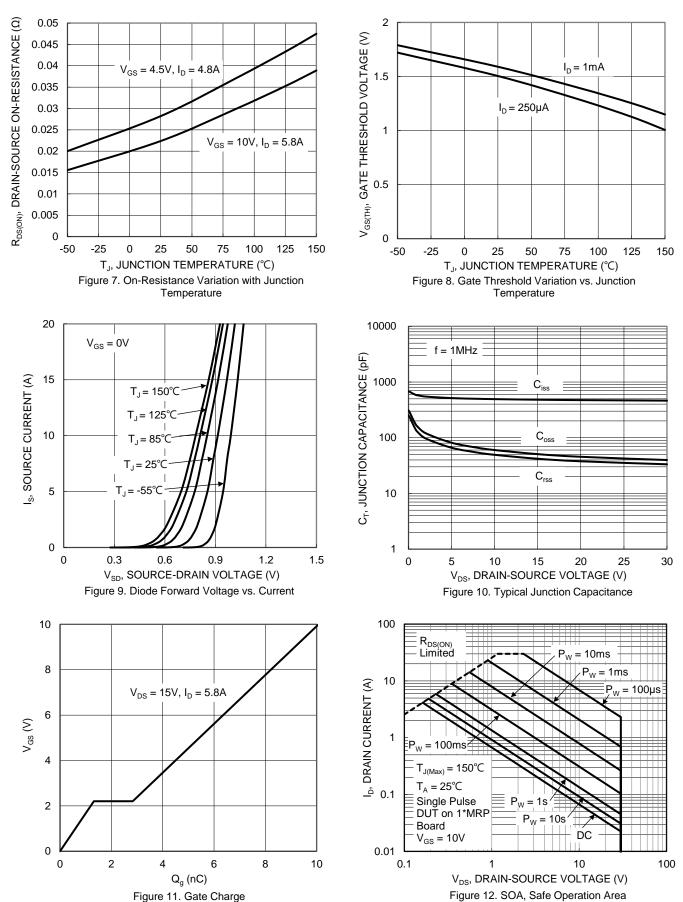
8. Guaranteed by design. Not subject to production testing.



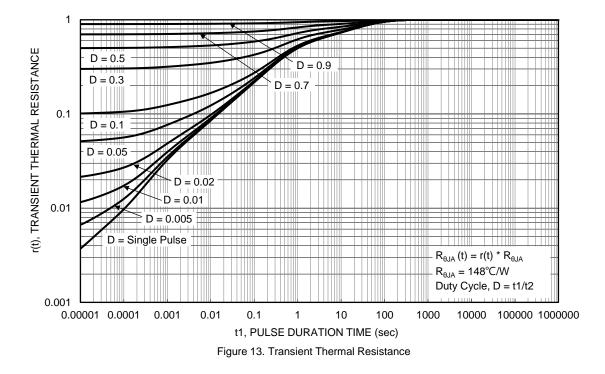
DMN3032L







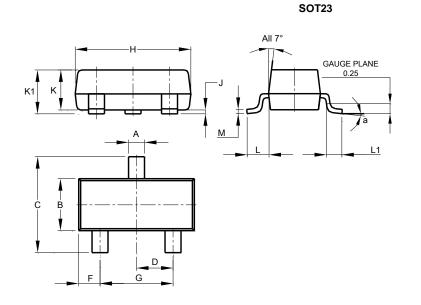






Package Outline Dimensions

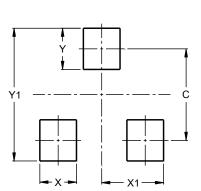
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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